

2N3010 Datasheet, Equivalent, Cross Reference Search

Type Designator: 2N3010

Material of Transistor: Si

Polarity: NPN

Maximum Collector Power Dissipation (P_c): 0.36 W

Maximum Collector-Base Voltage $|V_{cb}|$: 15 V

Maximum Collector-Emitter Voltage $|V_{ce}|$: 6 V

Maximum Emitter-Base Voltage $|V_{eb}|$: 4 V

Maximum Collector Current $|I_c \text{ max}|$: 0.05 A

Max. Operating Junction Temperature (T_j): 175 °C

Transition Frequency (f_t): 600 MHz

Collector Capacitance (C_c): 3 pF

Forward Current Transfer Ratio (hFE), MIN: 25

Noise Figure, dB: -

Package: TO18